

DFN3×3A-8L

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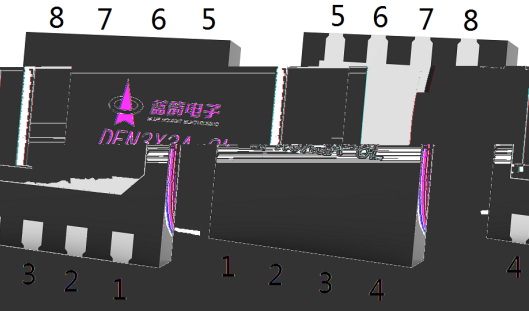
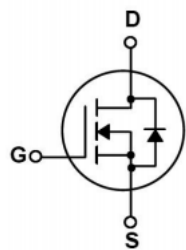
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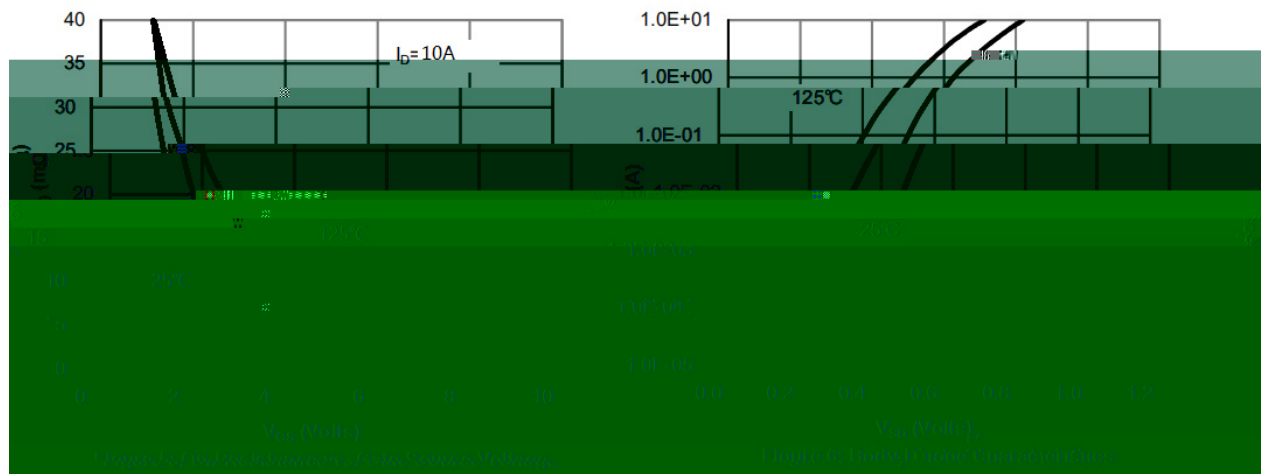
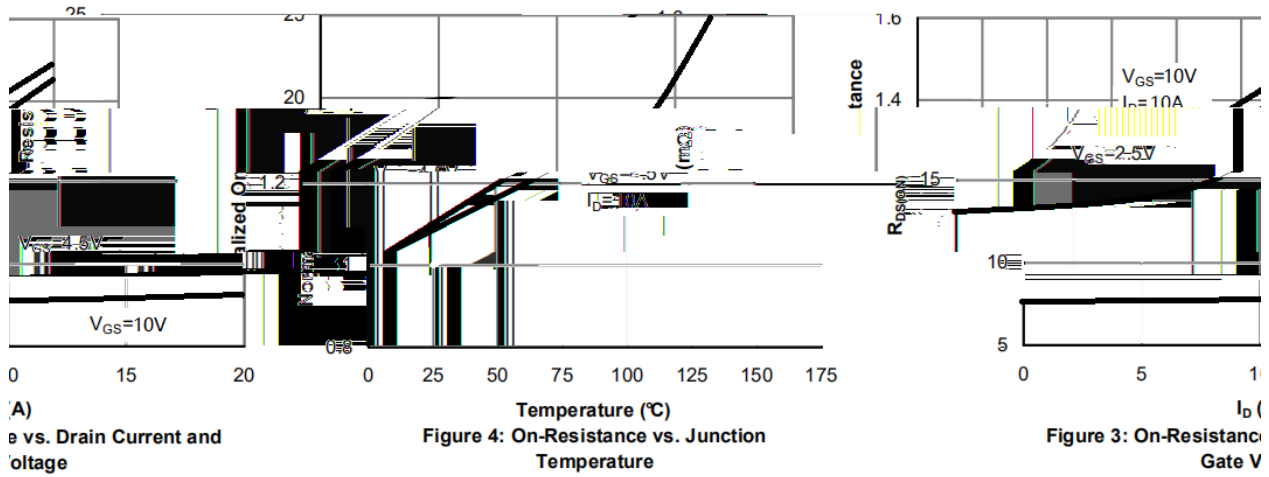
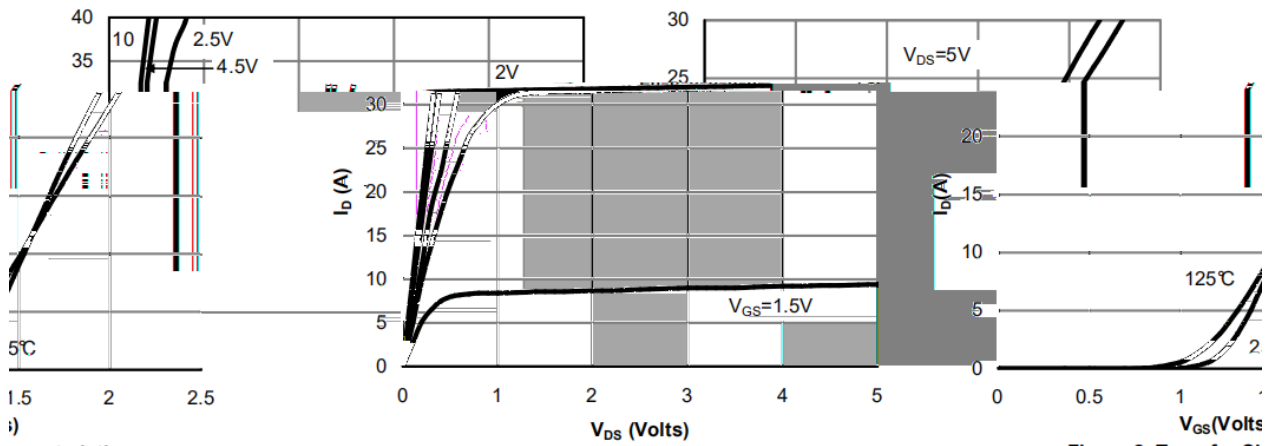
出脚	定义
Pin1	S
Pin2	S
Pin3	S
Pin4	G
Pin5	D
Pin6	D
Pin7	D
Pin8	D

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	20	V
Drain Current		$I_D(T_C=25^\circ\text{C})$	43	A
Drain Current - Pulsed		I_{DM}	107	A
Gate-Source Voltage		V_{GS}	± 12	V
Avalanche Current		I_{AS}	12.5	A
Single Pulsed Avalanche Energy		E_{AS}	111	mJ
Power Dissipation		$P_D(T_C=25^\circ\text{C})$	28	W
Junction Temperature Range		T_j	150	
Storage Temperature Range		T_{stg}	-55 150	
Maximum Junction-to-Ambient	$t \leq 10\text{s}$	$R_{\theta JA}$	50	/W
	Steady-State		70	
Maximum Junction-to-Case	Steady-State	$R_{\theta JC}$	4.5	/W

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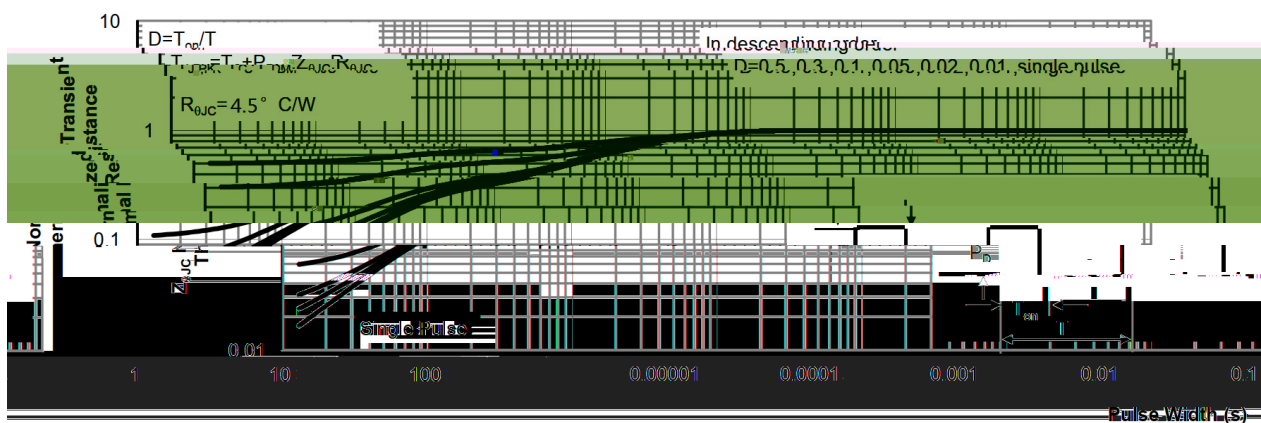
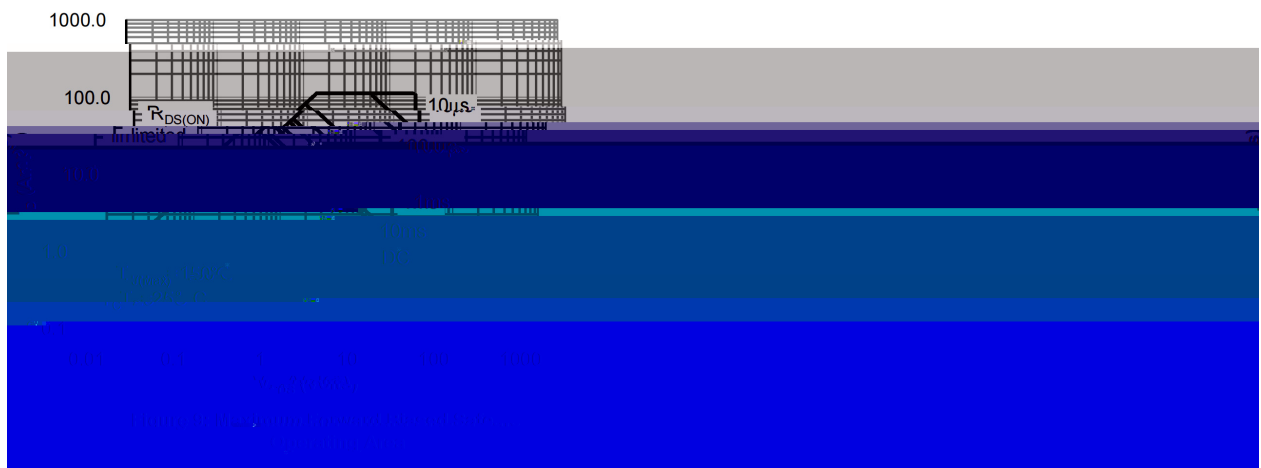
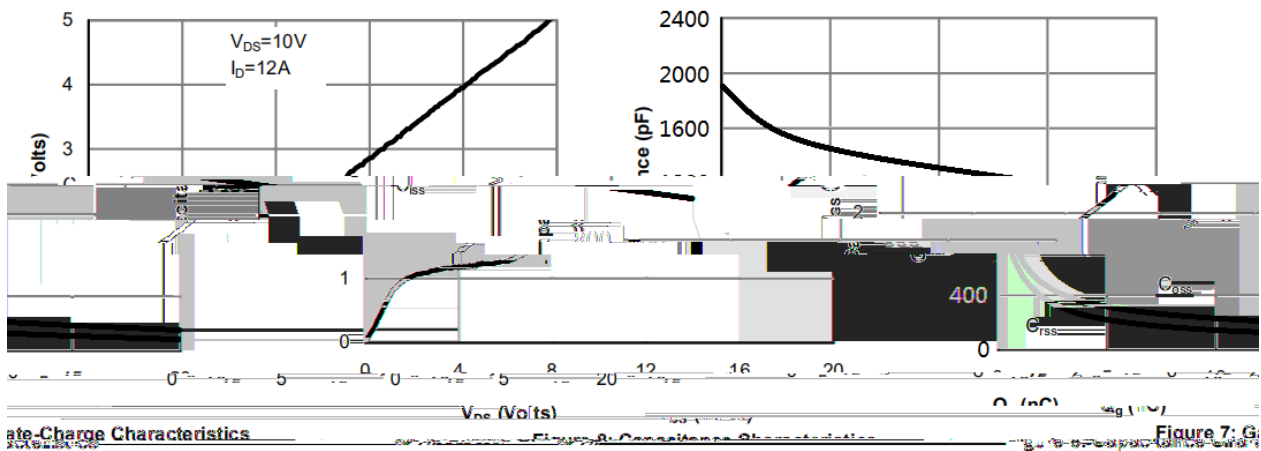
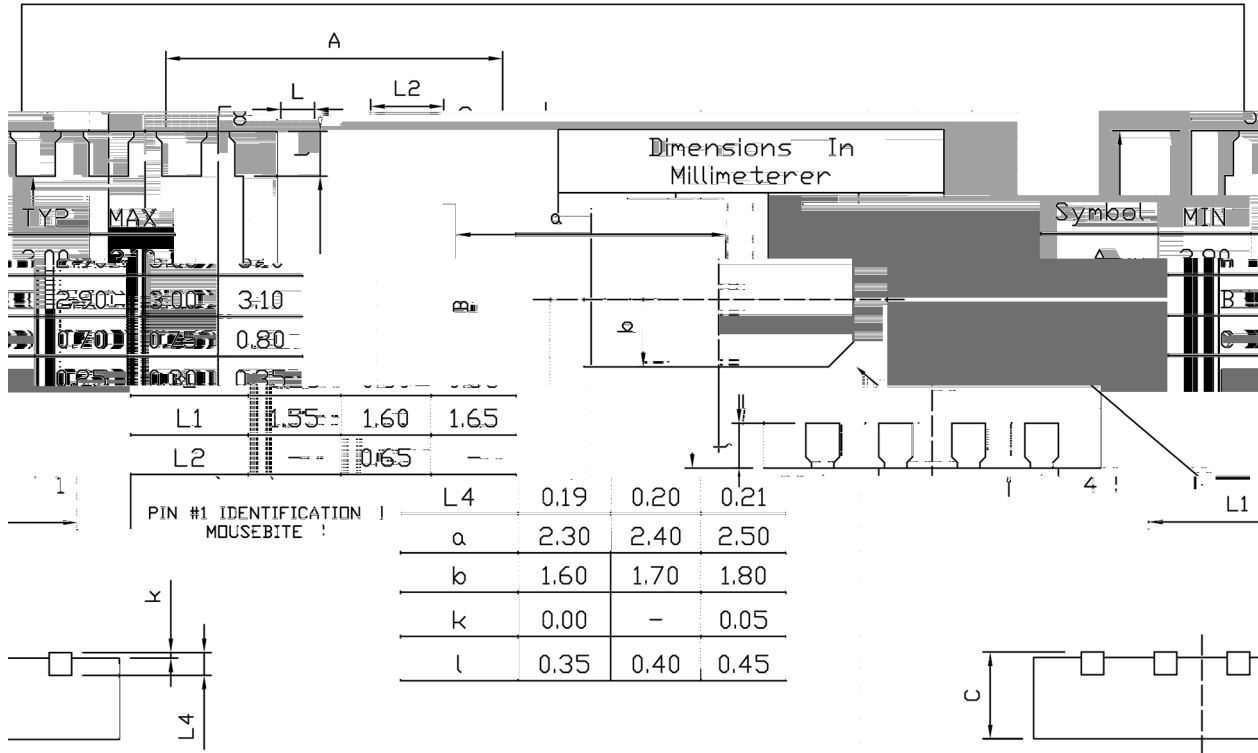


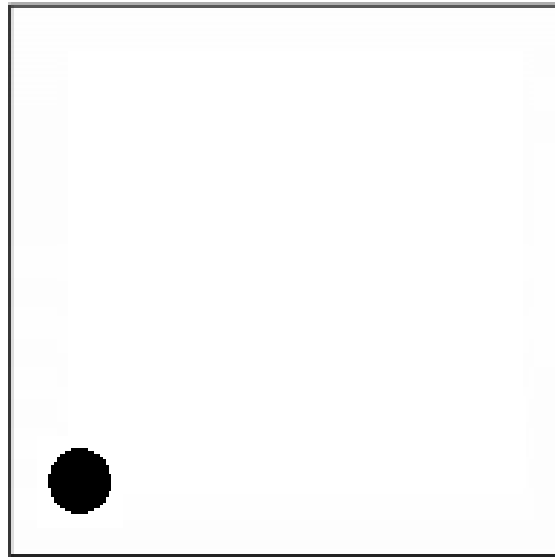
Figure 10: Normalized Maximum Transie

DFN3X3A-8L

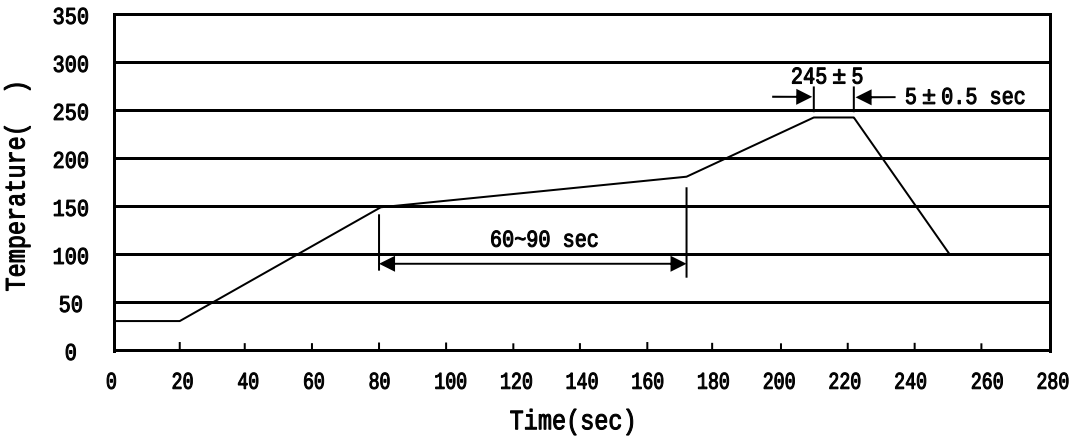
Unit:mm



Rev.00 202004



Temperature Profile for IR Reflow Soldering(Pb-Free)



± ± ± ±

± ±

	Units/Reel /	Reels/Inner Box /	Units/Inner Box /	Inner Boxes/Outer Box /	Units/Outer Box /	Reel	Inner Box	Outer Box
						"		